

N-Channel 40 V (D-S) MOSFET

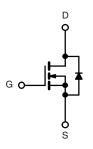
PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^a	Q _g (Typ.)			
40	0.0088 at V _{GS} = 10 V	50	16 nC			
40	0.0105 at V _{GS} = 4.5 V	50	10110			

FEATURES

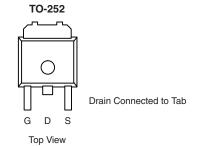
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % UIS Tested
- 100 % R_q Tested
- PWM Optimized
- Compliant to RoHS Directive 2002/95/EC



- LCD Display Backlight Inverters
- DC/DC Converters



N-Channel MOSFET



Ordering Information: SUD50N04-8m8P-4GE3 (Lead (Pb)-free and Halogen-free)

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	40	V		
Gate-Source Voltage	V _{GS}	± 20			
-	T _C = 25 °C		50 ^a		
Continuous Drain Current (T. 150 °C)	T _C = 70 °C		44		
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	- I _D	14 ^b		
	T _A = 70 °C		11.2 ^b		
Pulsed Drain Current	I _{DM}	100	Α		
Continuous Source-Drain Diode Current	T _C = 25 °C		40		
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	2.6 ^b		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	30		
Avalanche Energy	L = 0.1 IIII	E _{AS}	45	mJ	
	T _C = 25 °C		48.1	W	
Maximum Power Dissipation	T _C = 70 °C	D	30.8		
Maximum Fower Dissipation	T _A = 25 °C	- P _D	3.1 ^b		
	T _A = 70 °C		2.0 ^b		
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient ^b	Steady State	R _{thJA}	32	40	°C/W		
Maximum Junction-to-Case	Steady State	R _{thJC}	2.1	2.6	G/VV		

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.





SUD50N04-8m8P N-Channel

40 V (D-S) MOSFET

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	40			V	
$V_{\rm DS}$ Temperature Coefficient $\Delta V_{\rm DS}/T$		1 10 mA		44		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 1.0 mA		- 5.9		mv/°C	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.5		3.0	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}$	= 40 V, V _{GS} = 0 V		1		
Zero Gate Voltage Drain Current		$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 ^{\circ}\text{C}$			20	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	50			Α	
Drain-Source On-State Resistance ^a	D	V _{GS} = 10 V, I _D = 20 A		0.0069 0.0088		0	
Diani-30uice Oir-3iate nesistance"	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 15 A		0.0084	0.0105	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 15 A		75		S	
Dynamic ^b							
Input Capacitance	C _{iss}			2400		pF	
Output Capacitance	C _{oss}	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		260			
Reverse Transfer Capacitance	C _{rss}			100			
Total Cata Charge	Q _g	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$		37	56	nC	
Total Gate Charge				16	24		
Gate-Source Charge		$V_{DS} = 20 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 20 \text{ A}$		6.5			
Gate-Drain Charge	Q_{gd}			4.5			
Gate Resistance	R_{g}	f = 1 MHz	2.5	5.5	8.5	Ω	
Turn-On Delay Time	t _{d(on)}			30	45		
Rise Time	t _r	V_{DD} = 20 V, R_L = 1 Ω		15	25		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 20 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$		45	70		
Fall Time	t _f			15	25	ns	
Turn-On Delay Time	t _{d(on)}			9	15	115	
Rise Time	t _r	$V_{DD} = 20 \text{ V}, R_L = 1 \Omega$		5	10]	
urn-Off Delay Time t _{d(c}		$I_D \cong 20 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		40	60		
Fall Time	t _f			5	10		
Drain-Source Body Diode Characteris	tics						
Continuous Source-Drain Diode Current	l _S	T _C = 25 °C			40	Α	
Pulse Diode Forward Current ^a	I _{SM}				100	^	
Body Diode Voltage	V_{SD}	I _S = 10 A		0.81	1.2	V	
Body Diode Reverse Recovery Time				22	35	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	l _F = 20 A, dl/dt = 100 A/μs, T _{.l} = 25 °C		14	25	nC	
Reverse Recovery Fall Time	t _a	$\begin{bmatrix} 1 & -20 & A, & u & u & = 100 & A/\mu & 1, & 1 & = 25 & C \\ \end{bmatrix}$		11		ne	
Reverse Recovery Rise Time	t _b			11		ns	

Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.

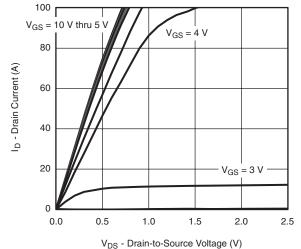
b. Guaranteed by design, not subject to production testing.

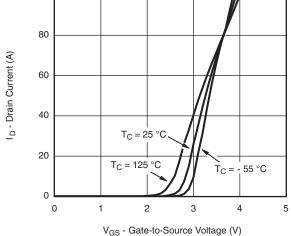


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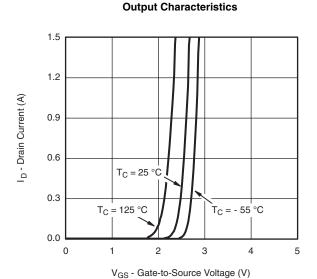
100

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

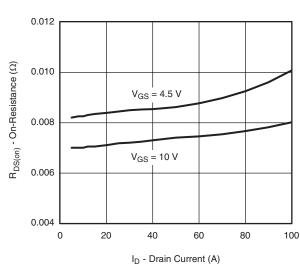




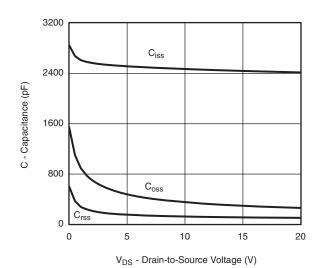
Transfer Characteristics



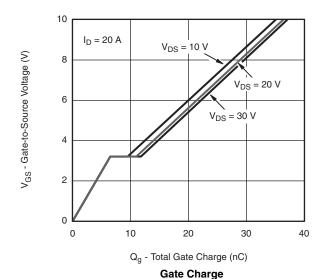
Transfer Characteristics



On-Resistance vs. Drain Current



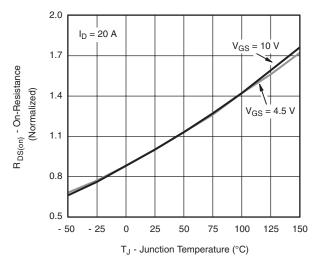
Capacitance



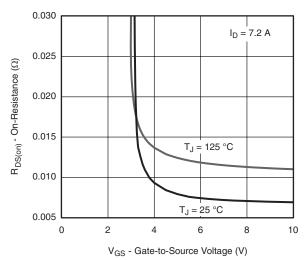


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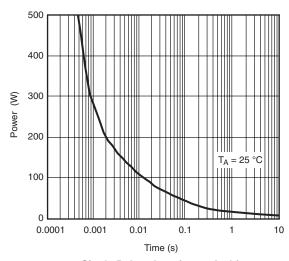
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



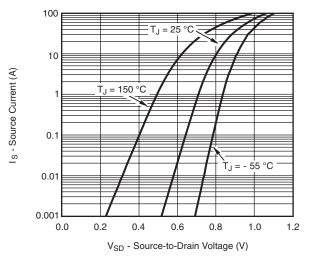
On-Resistance vs. Junction Temperature



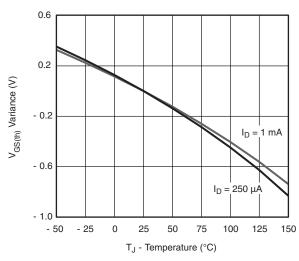
On-Resistance vs. Gate-to-Source Voltage



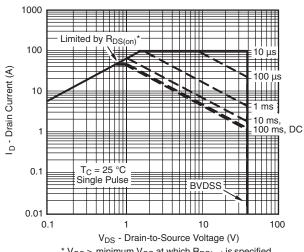
Single Pulse, Junction-to-Ambient



Source-Drain Diode Forward Voltage



Threshold Voltage

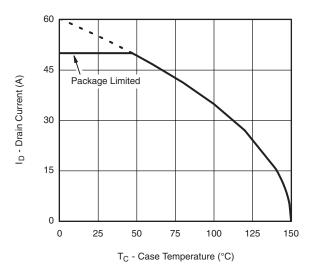


* V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

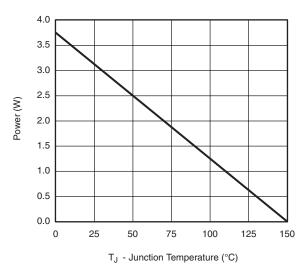
Safe Operating Area, Junction-to-Case

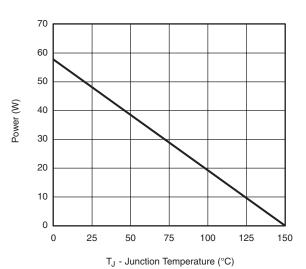
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*, Junction-to-Case





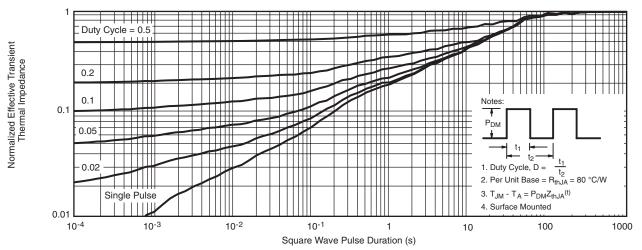
Power Derating, Junction-to-Ambient

Power Derating, Junction-to-Case

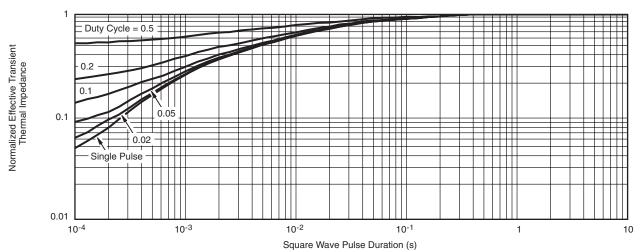
^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



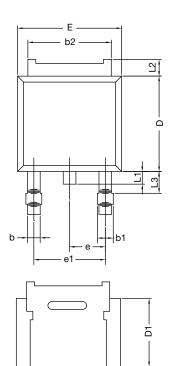
Normalized Thermal Transient Impedance, Junction-to-Ambient

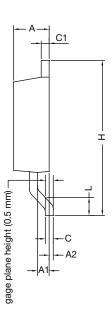


Normalized Thermal Transient Impedance, Junction-to-Case

N-Channel 40 V (D-S) MOSFET

TO-252AA CASE OUTLINE





	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
Е	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28 BSC		0.090 BSC		
e1	4.57 BSC		0.180 BSC		
Н	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347					

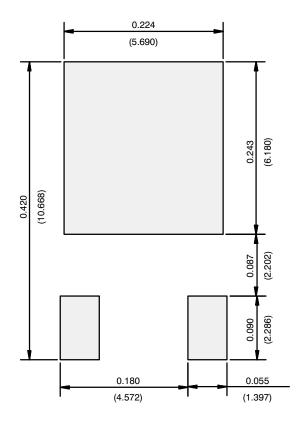
Note

• Dimension L3 is for reference only.

SUD50N04-8m8P N-Channel

40 V (D-S) MOSFET

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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SUD50N04-8m8P N-Channel 40 V (D-S) MOSFET

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